

— お詫びと訂正 —

学会誌掲載記事正誤表

日本銅学会誌「銅と銅合金」に掲載されました以下の論文で、一部内容に誤りがありました。会員の皆様に謹んでお詫びいたしますとともに、下記の通り訂正いたします。

● 日本銅学会誌 「銅と銅合金」 第64巻 1号 (2025) pp. 77-82.
「Cu/Cu₄Ti 複相合金線材の低温焼鈍硬化」 佛圓 大河 他

・ P. 79 Fig. 3 キャプション

誤	Fig. 3 Changes in electrical conductivity and Ti content dissolved in the Cu matrix of Cu-4.1 at.% Ti alloy wires, which were over-aged, wire-drawn, and then annealing at a low-temperature of 300 to 400°C, as a function of annealing time.
正	Fig. 3 Changes in electrical conductivity and Ti content dissolved in the Cu matrix of Cu-4.1 at.% Ti alloy wires, which were over-aged, wire-drawn, and then annealed at a low-temperature of 300 to 400°C, as a function of annealing time.

・ P. 81 Fig. 8 キャプション

誤	Fig. 8 TEM images of Cu-4.1 at.% Ti alloy wires (Φ0.1 mm): as-drawn (a) and low-temperature annealed at 400°C for 20 min (b), and 80 min (c). The arrows in (b) and (c) marks twin boundaries.
正	Fig. 8 TEM images of Cu-4.1 at.% Ti alloy wires (Φ0.1 mm): as-drawn (a) and low-temperature annealed at 400 °C for 20 min (b), and 80 min (c). The arrows in (b) and (c) mark twin boundaries.

・ P. 82 Fig. 9 キャプション

誤	Fig. 9 STEM-HAADF images of Cu-4.1 at.% Ti alloy wires (Φ0.1 mm): as-drawn (a) and low-temperature annealed at 400 °C for 20 min (c), 80 min (f). Ti mapping diagram by EDS analysis (Before low-temperature annealing: (b), 400 °C 20 min: (d), 400 °C 80 min: (f)).
正	Fig. 9 STEM-HAADF images of Cu-4.1 at.% Ti alloy wires (Φ0.1 mm): as-drawn (a) and low-temperature annealed at 400 °C for 20 min (c), 80 min (e). Ti mapping diagram by EDS analysis (Before low-temperature annealing: (b), 400 °C 20 min: (d), 400 °C 80 min: (f)).